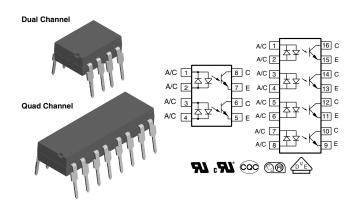


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Vishay Semiconductors

Optocoupler, Phototransistor Output, AC Input (Dual, Quad Channel)



DESCRIPTION

The ILD620, ILQ620, ILD620GB, and ILQ620GB are multi-channel input phototransistor optocouplers that use inverse parallel GaAs IRLED emitter and high gain NPN silicon phototransistors per channel. These devices are constructed using over/under leadframe optical coupling and double molded insulation resulting in a withstand test voltage of $5300\ V_{RMS}$.

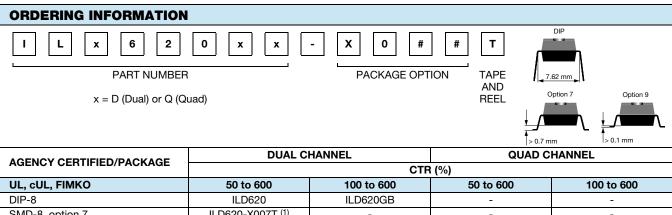
The LED parameters and the linear CTR characteristics make these devices well suited for AC voltage detection. The ILD620GB and ILQ620GB with its low $I_{\rm F}$ guaranteed CTR_{CEsat} minimizes power dissipation of the A_C voltage detection network that is placed in series with the LEDs. Eliminating the phototransistor base connection provides added electrical noise immunity from the transients found in many industrial control environments.

FEATURES

- · Identical channel to channel footprint
- ILD620 crosses to TLP620-2
- ILQ620 crosses to TLP620-4
- High collector emitter voltage, BV_{CEO} = 70 V
- Dual and quad packages feature:
 - Reduced board space
 - Lower pin and parts count
 - Better channel to channel CTR match
 - Improved common mode rejection
- Isolation test voltage 5300 V_{RMS}
- Material categorization: For definitions of compliance please see <u>www.vishay.com/doc?99912</u>

AGENCY APPROVALS

- UL1577, file no. E52744 system code H, double protection
- cUL tested to CSA 22.2 bulletin 5A
- DIN EN 60747-5-5 (VDE 0884)
- FIMKO
- CQC GB4943.1-2011 and GB8898:2011 (suitable for installation altitude below 2000 m)



AGENCY CERTIFIED/PACKAGE					
AGENCY CERTIFIED/PACKAGE		CTR	ł (%)		
UL, cUL, FIMKO	50 to 600	100 to 600	50 to 600	100 to 600	
DIP-8	ILD620	ILD620GB	-	-	
SMD-8, option 7	ILD620-X007T (1)	-	-	-	
SMD-8, option 9	ILD620-X009T (1)	ILD620GB-X009T (1)	-	-	
DIP-16	-	-	ILQ620	ILQ620GB	
SMD-16, option 7	-	-	ILQ620-X007	-	
SMD-16, option 9	-	-	ILQ620-X009T (1)	ILQ620GB-X009T (1)	
VDE, UL, cUL, FIMKO	50 to 600	100 to 600	50 to 600	100 to 600	
DIP-16	-	-	ILQ620-X001	-	
SMD-16, option 9	-	-	ILQ620-X019T (1)	-	

Notes

- Additional options may be possible, please contact sales office.
- (1) Also available in tubes, do not put T on the end.

Rev. 1.8, 12-Apr-13 Document Number: 83653

ILD620, ILD620GB, ILQ620, ILQ620GB

Vishay Semiconductors

ABSOLUTE MAXIMUM RAT	TEST CONDITION	PART	SYMBOL	VALUE	UNIT
	IESI CONDITION	PAKI	STINIBUL	VALUE	UNII
INPUT					
Forward current			I _F	± 60	mA
Surge current			I _{FSM}	± 1.5	Α
Power dissipation			P _{diss}	100	mW
Derate linearly from 25 °C				1.3	mW/°C
OUTPUT					
Collector emitter breakdown voltage			BV _{CEO}	70	V
Callastar august			I _C	50	mA
Collector current	t < 1 s		I _C	100	mA
Power dissipation			P _{diss}	150	mW
Derate from 25 °C				2	mW/°C
COUPLER					
Isolation test voltage	t = 1 s		V _{ISO}	5300	V _{RMS}
Isolation voltage			V _{IORM}	890	V _P
Total power dissipation			P _{tot}	250	mW
Dankana dianiantian		ILD620		400	mW
Package dissipation		ILD620GB		400	mW
Derate from 25 °C				5.33	mW/°C
Deal and distinction		ILQ620		500	mW
Package dissipation		ILQ620GB		500	mW
Derate from 25 °C				6.67	mW/°C
Creepage distance				≥ 7	mm
Clearance distance				≥ 7	mm
In the Control of the	V _{IO} = 500 V, T _{amb} = 25 °C		R _{IO}	≥ 10 ¹²	Ω
Isolation resistance	V _{IO} = 500 V, T _{amb} = 100 °C		R _{IO}	≥ 10 ¹¹	Ω
Storage temperature			T _{stg}	- 55 to + 150	°C
Operating temperature			T _{amb}	- 55 to + 100	°C
Junction temperature			T _i	100	°C
Soldering temperature (1)	2 mm from case bottom		T _{sld}	260	°C

Notes

- Stresses in excess of the absolute maximum ratings can cause permanent damage to the device. Functional operation of the device is not
 implied at these or any other conditions in excess of those given in the operational sections of this document. Exposure to absolute
 maximum ratings for extended periods of the time can adversely affect reliability.
- (1) Refer to reflow profile for soldering conditions for surface mounted devices (SMD). Refer to wave profile for soldering conditions for through hole devices (DIP).

ELECTRICAL CHARACTERISTICS (T _{amb} = 25 °C, unless otherwise specified)								
PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT	
INPUT								
Forward voltage	$I_F = \pm 10 \text{ mA}$		V _F	1	1.15	1.3	V	
Forward current	$V_R = \pm 0.7 V$		I _F		2.5	20	μA	
Capacitance	$V_F = 0 V$, $f = 1 MHz$		Co		25		pF	
Thermal resistance, junction to lead			R _{thJL}		750		K/W	
OUTPUT								
Collector emitter capacitance	V _{CE} = 5 V, f = 1 MHz		C _{CE}		6.8		pF	
Callacter emitter lackage august	V _{CE} = 24 V		I _{CEO}		10	100	nA	
Collector emitter leakage current	T _A = 85 °C, V _{CE} = 24 V		I _{CEO}		2	50	μA	
Thermal resistance, junction to lead			R _{thJL}		500		K/W	



ILD620, ILD620GB, ILQ620, ILQ620GB

Vishay Semiconductors

ELECTRICAL CHARACTERISTICS (T _{amb} = 25 °C, unless otherwise specified)								
PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT	
COUPLER								
Off-state collector current	$V_F = \pm 0.7 \text{ V}, V_{CE} = 24 \text{ V}$		I _{CEoff}		1	10	μΑ	
Collector emitter saturation voltage	$I_F = \pm 8 \text{ mA}, I_{CE} = 2.4 \text{ mA}$	ILD620	V _{CEsat}			0.4	V	
		ILQ620	V _{CEsat}			0.4	V	
	$I_F = \pm 1 \text{ mA}, I_{CE} = 0.2 \text{ mA}$	ILD620GB	V _{CEsat}			0.4	V	
		ILQ620GB	V _{CEsat}			0.4	V	

Note

 Minimum and maximum values are testing requirements. Typical values are characteristics of the device and are the result of engineering evaluation. Typical values are for information only and are not part of the testing requirements.

PARAMETER	ATIO (T _{amb} = 25 °C, unless ot TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT
Channel/channel CTR match	$I_F = \pm 5 \text{ mA}, V_{CE} = 5 \text{ V}$		CTRX/CTRY	1 to 1		3 to 1	
CTR symmetry	$I_{CE} (I_F = -5 \text{ mA})/I_{CE} (I_F = +5 \text{ mA})$		I _{CE(RATIO)}	0.5		2	
Current transfer ratio	I _F = ± 1 mA, V _{CE} = 0.4 V	ILD620	CTR _{CEsat}		60		%
(collector emitter saturated)		ILQ620	CTR _{CEsat}		60		%
Current transfer ratio	I _F = ± 5 mA, V _{CE} = 5 V	ILD620	CTR _{CE}	50	80	600	%
(collector emitter)		ILQ620	CTR _{CE}	50	80	600	%
Current transfer ratio	1 1 2 2 4 4 4 4 4 4 4 4 4 4 4 4 4 4 4 4	ILD620GB	CTR _{CEsat}	30			%
(collector emitter saturated)	$I_F = \pm 1 \text{ mA}, V_{CE} = 0.4 \text{ V}$	ILQ620GB	CTR _{CEsat}	30			%
Current transfer ratio	1 . 5 m A V . 5 V	ILD620GB	CTR _{CEsat}	100	200	600	%
(collector emitter)	$I_F = \pm 5 \text{ mA}, V_{CE} = 5 \text{ V}$	ILQ620GB	CTR _{CEsat}	100	200	600	%

SAFETY AND INSULATIO	N RATED PARAMETERS					
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Partial discharge test voltage - routine test	100 %, t _{test} = 1 s	V _{pd}	1.669			kV
Partial discharge test voltage -	$t_{Tr} = 60 \text{ s}, t_{test} = 10 \text{ s},$	V _{IOTM}	10			kV
lot test (sample test)	(see figure 2)	V _{pd}	1.424			kV
	V _{IO} = 500 V	R _{IO}	10 ¹²			Ω
Insulation resistance	V _{IO} = 500 V, T _{amb} = 100 °C	R _{IO}	10 ¹¹			Ω
Insulation resistance	V _{IO} = 500 V, T _{amb} = 150 °C (construction test only)	R _{IO}	10 ⁹			Ω
Forward current		I _{si}			275	mA
Power dissipation		P _{SO}			400	mW
Rated impulse voltage		V _{IOTM}			10	kV
Safety temperature		T _{si}			175	°C

Note

 According to DIN EN 60747-5-5 (VDE 0884) (see figure 2). This optocoupler is suitable for safe electrical isolation only within the safety ratings. Compliance with the safety ratings shall be ensured by means of suitable protective circuits.

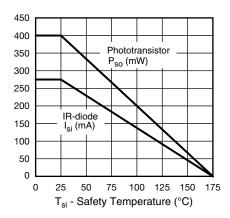


Fig. 1 - Derating Diagram

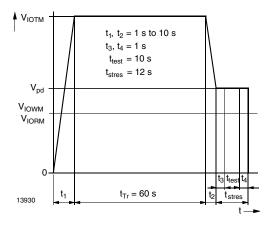


Fig. 2 - Test Pulse Diagram for Sample Test According to DIN EN 60747-5-2 (VDE 0884); IEC 60747-5-5

PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
NON-SATURATED	·					
On time	$I_F = \pm 10 \text{ mA}, V_{CC} = 5 \text{ V},$ $R_L = 75 \Omega, 50 \% \text{ of } V_{PP}$	t _{on}		3		μs
Rise time	$I_F = \pm 10 \text{ mA}, V_{CC} = 5 \text{ V},$ $R_L = 75 \Omega, 50 \% \text{ of } V_{PP}$	t _r		20		μs
Off time	$I_F = \pm 10 \text{ mA}, V_{CC} = 5 \text{ V},$ $R_L = 75 \Omega, 50 \% \text{ of V}_{PP}$	t _o ff		2.3		μs
Fall time	$I_F = \pm 10 \text{ mA}, V_{CC} = 5 \text{ V},$ $R_L = 75 \Omega, 50 \% \text{ of V}_{PP}$	t _f		2		μs
Propagation H to L	$I_F = \pm 10 \text{ mA}, V_{CC} = 5 \text{ V},$ $R_L = 75 \Omega, 50 \% \text{ of V}_{PP}$	t _{PHL}		1.1		μs
Propagation L to H	$I_F = \pm 10 \text{ mA}, V_{CC} = 5 \text{ V},$ $R_L = 75 \Omega, 50 \% \text{ of V}_{PP}$	t _{PLH}		2.5		μs
SATURATED	·					
On time	$I_F = \pm 10$ mA, $V_{CC} = 5$ V, $R_L = 1$ k Ω , $V_{TH} = 1.5$ V,	t _{on}		4.3		μs
Rise time	$I_F = \pm 10$ mA, $V_{CC} = 5$ V, $R_L = 1$ k Ω , $V_{TH} = 1.5$ V,	t _r		2.8		μs
Off time	$I_F = \pm 10$ mA, $V_{CC} = 5$ V, $R_L = 1$ k Ω , $V_{TH} = 1.5$ V,	t _o ff		2.5		μs
Fall time	$I_F = \pm 10$ mA, $V_{CC} = 5$ V, $R_L = 1$ k Ω , $V_{TH} = 1.5$ V,	t _f		11		μs
Propagation H to L	$I_F = \pm 10$ mA, $V_{CC} = 5$ V, $R_L = 1$ k Ω , $V_{TH} = 1.5$ V,	t _{PHL}		2.6		μs
Propagation L to H	$I_F = \pm 10$ mA, $V_{CC} = 5$ V, $R_L = 1$ k Ω , $V_{TH} = 1.5$ V,	t _{PLH}		7.2		μs

TYPICAL CHARACTERISTICS (T_{amb} = 25 °C, unless otherwise specified)

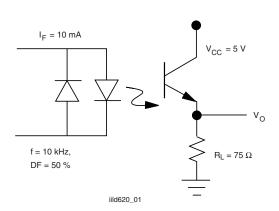


Fig. 3 - Non-Saturated Switching Timing

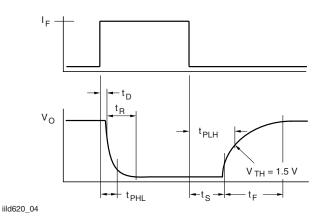


Fig. 6 - Saturated Switching Timing

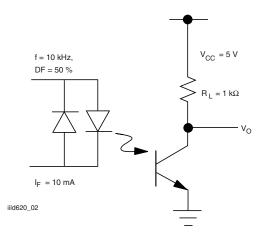


Fig. 4 - Saturated Switching Timing

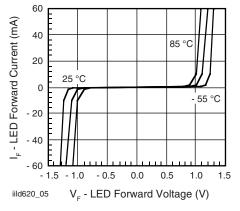


Fig. 7 - LED Forward Current vs.Forward Voltage

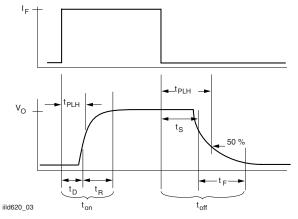


Fig. 5 - Non-Saturated Switching Timing

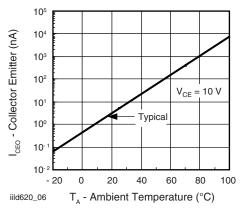


Fig. 8 - Collector Emitter Leakage vs. Temperature

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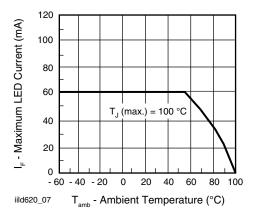


Fig. 9 - Maximum LED Current vs. Ambient Temperature

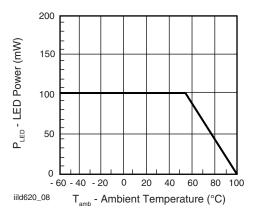


Fig. 10 - Maximum LED Power Dissipation

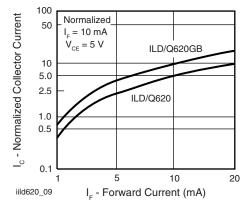


Fig. 11 - Collector Current vs. Diode Forward Current

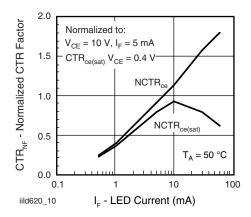


Fig. 12 - Normalization Factor for Non-Saturated and Saturated CTR vs. $I_{\rm F}$

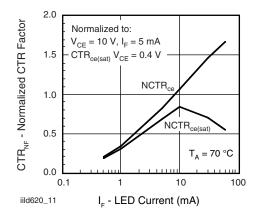


Fig. 13 - Normalization Factor for Non-Saturated and Saturated CTR vs. I_F

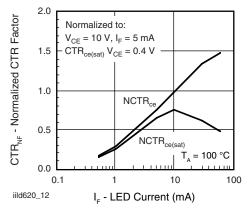


Fig. 14 - Normalization Factor for Non-Saturated and Saturated CTR vs. I_F

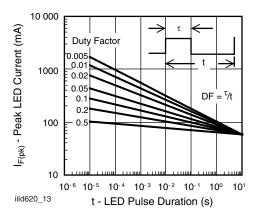


Fig. 15 - Peak LED Current vs. Pulse Duration, τ

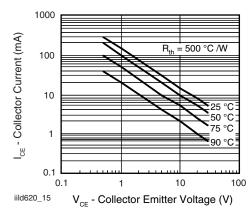


Fig. 17 - Maximum Collector Current vs. Collector Voltage

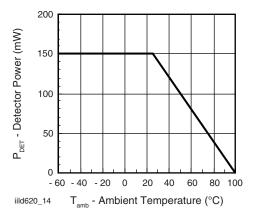
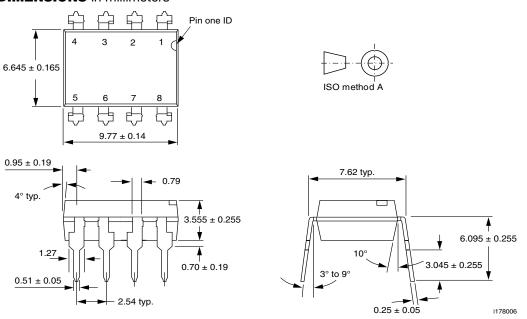


Fig. 16 - Maximum Detector Power Dissipation

PACKAGE DIMENSIONS in millimeters

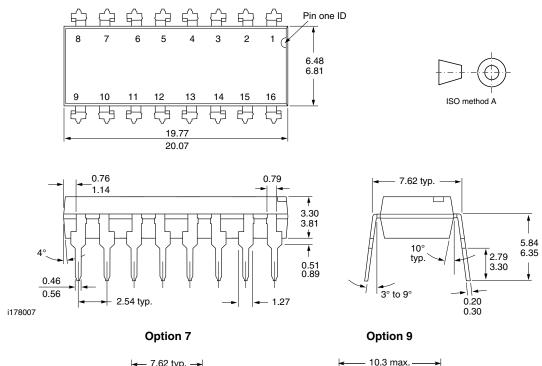


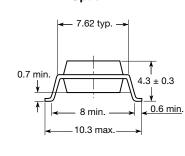
Rev. 1.8, 12-Apr-13 7 Document Number: 83653

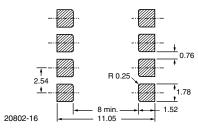


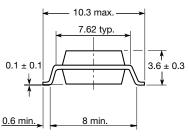
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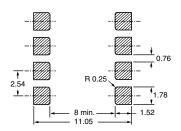
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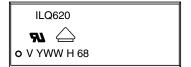






PACKAGE MARKING (example)





Notes

- Only option 1 and 7 reflected in the package marking.
- The VDE logo is only marked on option 1 parts.
- Tape and reel suffix (T) is not part of the package marking.



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